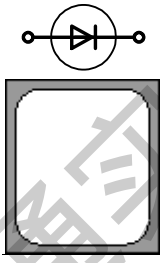


Type	Ag* Al*	V _{RRM} [V]	I _F [A]	Chip Size [mm] x [mm]	Package Options
DWLP 8	<input checked="" type="checkbox"/> <input checked="" type="checkbox"/>	400	6	3.60 1.80	sawn on foil <input checked="" type="checkbox"/> unsawn wafer <input checked="" type="checkbox"/> * in waffle pack <input checked="" type="checkbox"/>

*Frontside options

*Please contact IXYS chip sales



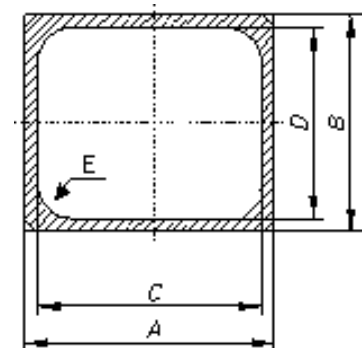
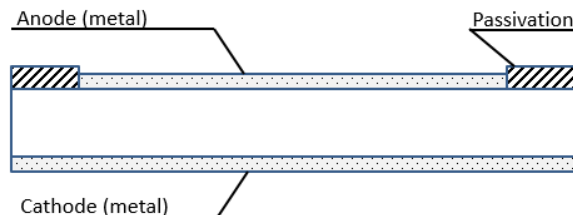
Mechanical Parameters

Area active	2.40 mm ²	Features: <ul style="list-style-type: none"> • Anode top • Pt doped • Epitaxial diode • Planar surface • Glass passivated Applications: <ul style="list-style-type: none"> • Antiparallel diode for high frequency switching devices • Antisaturation diode • Snubber diode • Free wheeling diode in converters and motor control circuits • Rectifiers in switch mode power supplies (SMPS) • Inductive heating • Uninterruptible power supplies (UPS) • Ultrasonic cleaners and welders • PDP
Area total	6.48 mm ²	
Wafer size Ø	150 mm	
Thickness	345 µm	
Material	Si	
Max. possible chips per wafer	2362	
Passivation front side	Glass	
Metallization top side	bondable or solderable	
Metallization backside	solderable (only): Al / Ti / Ni / Ag	
Recom. wire bonds (Al)	Anode Number 1 Ø 380 µm	
Reject Ink Dot Size	Ø 0.4-1.0 mm	
Recom. Storage Environment		
sawn on foil	in org. container, in dry nitrogen	< 6 month
unsawn wafer	in org. container, in dry nitrogen	< 2 year
in waffle pack	in org. container, in dry nitrogen	< 2 year
T _{stg}		-40 ... 40 °C

*Sinterable top/bottom side on request

Dimensions

A	B	C	D	E
[mm]	[mm]	[mm]	[mm]	[mm]
3.60	1.80	2.70	0.90	0.20



Electrical parameters

Symbol	Conditions	Ratings		
		min.	typ.	max.
I_R	$V = V_{RRM}$ $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 150^\circ\text{C}$			10 μA
				0.25 mA
V_F	$I_F = 6\text{ A}$ $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 150^\circ\text{C}$			1.40 V
				0.97 V
V_{FO}	For power-loss calculations only			0.72 V
r_F	$T_{VJ} = 175^\circ\text{C}$			26.60 m Ω
T_{VJ}		-55		175 $^\circ\text{C}$
$I_{F(AV)}$ *	$T_C = 125^\circ\text{C}; 180^\circ\text{ rect.}$			A
I_{FSM} *	$T_{VJ} = 45^\circ\text{C}; t = 10\text{ ms (50 Hz), sine}$			60 A
R_{thJC} *	DC current			2.5 K/W
t_{rr}	$V_R = 30$ $I_F = 1\text{ A}; -di_F/dt = 50\text{ A}/\mu\text{s}; T_{VJ} = 25^\circ\text{C}$		30	ns
I_{RM}	$V_R = 100$ $I_F = 12\text{ A}; -di_F/dt = 100\text{ A}/\mu\text{s}; T_{VJ} = 25^\circ\text{C}$			1.40 A

* Data according to assembled Chip

Data according to IEC 60747

Terms of Conditions and Usage

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Should you intend to use the product in aviation applications, in health or life endangering or life support applications, please notify. For any such applications we urgently recommend

- to perform joint risk and quality assessments;

- the conclusion of quality agreements;

- to establish joint measures to ensure application specific product capabilities and notify that IXYS may delivery dependent on the realization of any such measures.